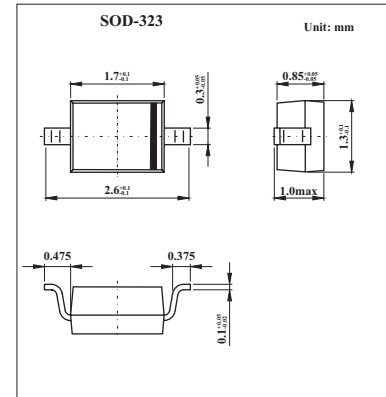


## Silicon Epitaxial Planar Diode

## KDV287

## ■ Features

- High Capacitance Ratio :  $C_{2V}/C_{25V}=7.6$ (Typ.)
- Low Series Resistance :  $r_s=1.9\ \Omega$  (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

■ Absolute Maximum Ratings  $T_a = 25\ ^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Peak Reverse Voltage	$V_{RM}$	35 ( $R_L=10K\ \Omega$ )	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25\ ^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1\ \mu\text{A}$	30			V
Reverse Current	$I_R$	$V_R = 28\ \text{V}$			10	nA
Capacitance	$C_{2V}$	$f = 1\ \text{MHz}; V_R = 2\ \text{V}$	4.2		5.7	pF
	$C_{25V}$	$f = 1\ \text{MHz}; V_R = 25\ \text{V}$	0.53		0.68	
Capacitance Ratio	$C_{2V}/C_{25V}$		7.3			
Series Resistance	$r_s$	$V_R = 5\ \text{V}, f = 470\ \text{MHz}$		1.9	2.3	$\Omega$

Note :

Available in matched group for capacitance to 6%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.06$$

( $V_R=2\sim 25\text{V}$ )

## ■ Marking

Marking	UP
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